

SELECTIVE EPITAXY VERTICAL INTEGRATED CIRCUIT

COMPONENTS AND METHODS

Abstract

Integrated circuit components are described that are formed using selective epitaxy such that the integrated circuit components, such as transistors, are vertically oriented. These structures have regions that are doped in situ during selective epitaxial growth of the component body. These components are grown directly in electrical communication lines. Moreover, these components are adapted for use in memory devices and are believed to not require the use of shallow trench isolation.

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